Xiao Yu

List of Publications by Year
in descending order

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citing authors

#	Article	IF	Citations
1	HfO₂-ZrO₂ Superlattice Ferroelectric Capacitor With Improved Endurance Performance and Higher Fatigue Recovery Capability. IEEE Electron Device Letters, 2022, 43, 216-219.	3.9	33
2	Analog Synapses Based on Nonvolatile FETs With Amorphous ZrO₂ Dielectric for Spiking Neural Network Applications. IEEE Transactions on Electron Devices, 2022, 69, 1028-1033.	3.0	12
3	Impact of post metallization annealing (PMA) on the electrical properties of Ge nMOSFETs with ZrO2 dielectric. Solid-State Electronics, 2022, 190, 108240.	1.4	0
4	Effect of thickness scaling on the switching dynamics of ferroelectric HfO2â€“ZrO2 capacitors. Ceramics International, 2022, 48, 28489-28495.	4.8	2
5	All-Optical Synapse With Directional Coupler Structure Based on Phase Change Material. IEEE Photonics Journal, 2021, 13, 1-6.	2.0	3
6	Ge N-Channel MOSFETs with ZrO2 Dielectric Achieving Improved Mobility. Nanoscale Research Letters, 2021, 16, 125.	5.7	5
7	Ferroelectric-Like Non-Volatile FET With Amorphous Gate Insulator for Supervised Learning Applications. IEEE Journal of the Electron Devices Society, 2021, 9, 1145-1150.	2.1	4
8	Direct-Bandgap Electroluminescence From Germanium With Subband Engineering Utilizing a Metal-Oxide-Semiconductor Structure. IEEE Transactions on Electron Devices, 2020, 67, 2016-2021.	3.0	1
9	Compact models for influential nodes identification problem in directed networks. Chaos, 2020, 30, 053126.	2.5	6
10	Ultra-Fast (ns-Scale) Characterization of NBTI Behaviors in Si pFinFETs. IEEE Journal of the Electron Devices Society, 2020, 8, 577-583.	2.1	8
11	A Fast V_{th} Measurement (FVM) Technique for NBTI Behavior Characterization. IEEE Electron Device Letters, 2018, 39, 172-175.	3.9	11
12	Back-Gate Modulation in UTB GeOI pMOSFETs With Advanced Substrate Fabrication Technique. IEEE Transactions on Electron Devices, 2018, 65, 895-900.	3.0	8
13	Quantitative Characterization of Fast-Trap Behaviors in Al₂O₃/GeO_x/Ge pMOSFETs. IEEE Transactions on Electron Devices, 2018, 65, 2729-2735.	3.0	3
14	Real-Time Polarization Switch Characterization of HfZrO₄ for Negative Capacitance Field-Effect Transistor Applications. IEEE Electron Device Letters, 2018, 39, 1469-1472.	3.9	15
15	Investigation of Self-Heating Effect on Ballistic Transport Characterization for Si FinFETs Featuring Ultrafast Pulsed IV Technique. IEEE Transactions on Electron Devices, 2017, 64, 909-915.	3.0	14
16	Experimental Investigation of Ballistic Carrier Transport for Sub-100-nm Ge n-MOSFETs. IEEE Electron Device Letters, 2017, 38, 434-437.	3.9	7
17	Evaluation of Mobility Degradation Factors and Performance Improvement of Ultrathin-Body Germanium-on-Insulator MOSFETs by GOI Thinning Using Plasma Oxidation. IEEE Transactions on Electron Devices, 2017, 64, 1418-1425.	3.0	10
18	Ultrafast pulse characterization of hot carrier injection effects on ballistic carrier transport for sub-100 nm MOSFETs. , 2017, , .		6

#	Article	IF	Citations
19	Electrical Properties of Ge pMOSFETs With Ultrathin EOT HfO₂/AlO_{<italic>x</italic>}/GeO_{<italic>x</italic>}Gate-Stacks and NiGe Metal Source/Drain. IEEE Transactions on Electron Devices, 2017, 64, 4831-4837.	3.0	5
20	Ultra fast (<1 ns) electrical characterization of self-heating effect and its impact on hot carrier injection in 14nm FinFETs. , 2017, , .		30
21	Aggressive EOT Scaling of Ge pMOSFETs With HfO₂/AlO_{<italic>x</italic>}/GeO_{<italic>x</italic>}Gate-Stacks Fabricated by Ozone Postoxidation. IEEE Electron Device Letters, 2016, 37, 831-834.	3.9	50
22	Impact of Postdeposition Annealing Ambient on the Mobility of Ge nMOSFETs With 1-nm EOT Al₂O₃/GeO_{<i>x</i>}/Ge Gate-Stacks. IEEE Transactions on Electron Devices, 2016, 63, 558-564.	3.0	11
23	Characterization of ultrathin-body Germanium-on-insulator (GeOI) structures and MOSFETs on flipped Smart-Cutâ„¢ GeOI substrates. Solid-State Electronics, 2016, 115, 120-125.	1.4	15
24	Impact of back interface passivation on electrical properties of ultrathin-body Germanium-on-insulator (GeOI) MOSFETs. Microelectronic Engineering, 2015, 147, 196-200.	2.4	16
25	Impact of Channel Orientation on Electrical Properties of Ge p- and n-MOSFETs With 1-nm EOT Al₂O₃/GeO_x/Ge Gate-Stacks Fabricated by Plasma Postoxidation. IEEE Transactions on Electron Devices, 2014, 61, 3668-3675.	3.0	24
26	Impact of Plasma Postoxidation Temperature on the Electrical Properties of ${m Al}_{2}{m O}_{3}/{m GeO}_{x}/{m Ge}$ pMOSFETs and nMOSFETs. IEEE Transactions on Electron Devices, 2014, 61, 416-422.	3.0	34